PTO/SB/08A (10-01)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 10

Complete if Known	
Application Number	10/627,302
Filing Date	7/24/03
First Named Inventor	Patel. et al
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092-US

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
BNJ	AA	US- 3,511,727	05-12-1970	Hays, R.G.	
	AB	US- 4,190,488	02-26-1980	Winters, H.F.	
	AC	US- 4,310,380	12-12-1982	Flamm et al.	
	AD	US- 4,498,953	02-12-1985	Cook et al.	
	AE	US- 4,695,700	09-22-1987	Provence et al.	
	AF	US- 4,740,410	04-26-1988	Muller et al.	
	AG	US- 4,749,440	06-07-1988	Blackwood et al.	
	AH	US- 4,789,426	12-06-1988	Pipkin, M.A.	
	AI	US- 5,206,471	04-27-1993	Smith, D.K.	
	AJ	US- 5,330,301	07-19-1994	Brancher, C.D.	
	AK	US- 5,439,553	08-08-1995	Grant et al.	
	AL	US- 5,534,107	07-09-1996	Gray et al.	
	AM	US- 5,672,242	09-30-1997	Jen,	
	AN	US- 5,716,495	02-10-1998	Butterbaugh et al.	
	AO	US- 5,726,480	03-10-1998	Pister, K.S.	
	AP	US- 5,753,073	05-19-1998	Jen,	
	AQ	US- 5,757,456	05-26-1998	Yamazaki et al.	
	AR	US- 5,835,256	11-10-1998	Huibers, A.	
	AS	US- 5,858,065	01-12-1999	Li et al.	
BNJ	AT	US- 6,436,229	08-20-2002	Tai et al.	

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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] -Number[4]- Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
BNJ	BA	EP-0704884-A2	04-03-1996	Mehta, J.		
	BB	EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
	BC	EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
	BD	EP-0838839-A2	04-29-1998	Bhardwai, J.K.		
	BE	EP-0878824-A2	11-18-1998	McQuarrie et al.		
	BF	EP-0878824-A3	01-19-2000	McQuarrie et al.		
	BG	EP-0955668-A2	11-10-1999	Yao et al.		
	BH	WO-98/05605	02-12-1998	Bhardwai, J.K.		
	BI	WO-98/13856	04-02-1998	Bhardwai, J.K.		
BNJ	BJ	WO-98/32163	07-23-1998	Tai et al.		

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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Sheet 2 of 10

Complete if Known	
Application Number	10/627,302
Filing Date	7/24/03
First Named Inventor	Patel. et al
Art Unit	Not Yet Assigned
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Attorney Docket Number	P092-US

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BNT	AU	US- 6,051,503	04-18-2000	Bhardwaj, J.K.	
	AV	US- 6,162,367	12-19-2000	Tai et al.	
	AW	US- 6,277,173 B1	08-21-2001	Sadakata et al.	
	AX	US- 6,290,864 B1	09-18-2001	Patel et al.	
	AY	US- 6,328,801 B1	12-11-2001	Gary et al.	
	AZ	US- 6,334,928 B1	03-12-2002	Sekine et al.	
	AAA	US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
	AAB	US- 2001/0002663 A1	06-07-2001	Tai et al.	
	AAC	US- 2002/0033229 A1	03-21-2002	Lebouitz et al.	
		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
		US- 2003/0054588 A1	03-20-2003	Patel, et al.	
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		US- 5,835,293	11-10-1998	Min, et al.	
		US- 5,917,045	06-29-1999	Lewis, et al.	
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		US- 5,757,539	05-26-1998	Min	
BNT		US- 6,197,610 B1	03-06-2001	Toda	

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BNT	BK	WO-99/01887	01-14-1999	Lea et al.		
	BL	WO-99/03313	01-21-1999	Lea et al.		
	BM	WO-99/49506	09-30-1999	McQuarrie, A.D.		
	BN	WO-00/52740	08-08-2000	Bhardwaj et al.		
	BO	JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.		
	BP	JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
	BQ	JP-1985/60057938-A	04-03-1985	Katsumi et al.		
	BR	JP-1986/61053732-A	03-17-1986	Arata et al.		
	BS	JP-1986/61134019-A	06-21-1986	Shinji et al.		
BNT	BT	JP-1986/61181131-A	08-13-1986	Shinji et al.		

Examiner Signature		Date Considered	8/2/04

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Sheet 3 of 10

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First Named Inventor	Patel, et al
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092-US

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BNT		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
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		US- 6,449,079	09-10-2002	Herrmann	
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		US- 6,204,080	03-20-2001	Hwang	
		US- 5,696,620	12-09-1997	Kim	
		US- 5,701,192	12-23-1997	Ji, et al.	
		US- 5,702,569	12-30-1997	Park, et al.	
		US- 5,774,256	06-30-1998	Min, et al.	
		US- 5,822,109	10-13-1998	Jeon	
BNT		US-			

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BNT	BU	JP-1986/61187238-A	08-20-1986	Nobuo et al.		
	BV	JP-1986/61270830-A	12-01-1986	Toru, T.		
	BW	JP-1987/62071217-A	04-01-1987	Toru et al.		
	BX	JP-1988/63155713-A	06-28-1988	Tadashi, F.		
	BY	JP-1989/01208834-A	08-22-1989	Nobuo et al.		
	BZ	JP-1989/10217921-A	08-31-1989	Tsuneo et al.		
	CA	JP-1990/02250323-A	10-08-1990	Susumu et al.		
	CB	JP-1991/03012921-A	01-21-1991	Nobuo et al.		
	CC	JP-1992/04096222-A	03-27-1992	Atsuyuki, A.		
BNT	CD	JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 4 of 10

Complete if Known	
Application Number	10/627,302
Filing Date	7/24/03
First Named Inventor	Patel. et al
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092-US

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BNT		US- 2002/0164879 A1	11/07/02	Leung, et al.	
		US- 2002/0163051 A1	11/07/02	Gopal, et al.	
		US- 2003/0077878 A1	04/24/03	Kumar, et al.	
		US- 2003/0124848 A1	0703/03	Chinn, et al.	
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		US- 2003/0219986 A1	11/27/03	Rattner, et al.,	
		US- 6,576,489 B2	06/10/03	Leung, et al.	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	
		US- 6,500,356 B2	12/31/02	Goto, et al.	
		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
		US- 2002/0024641 A1	02/28/02	Ilkov, et al.	
		US- 6,523,961 B2	02/25/03	Ilkov, et al.	
		US- 2003/0234994 A1	12/25/03	Pan	
BNT		US- 2004/0004753 A1	01/08/04	Pan	
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BNT	CE	JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
	CF	JP-1998/10313128-A	11-24-1998	Hanmin et al.		
	CG	JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		WO 2004/000720 A1	12/31/03	Pan, et al.		
BNT		WO 2004/001487 A2	12/31/03	Pan, et al.		

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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Sheet 5 of 10

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Application Number	10/627,302
Filing Date	7/24/03
First Named Inventor	Patel. et al
Group Art Unit	Not Yet Assigned
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
BNT	DA	ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
	DB	GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
	DC	HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
	DD	HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO2 Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
	DE	HOULE, F.A., "Dynamics of SiF4 Desorption During Etching of Silicon by XeF2", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
	DF	FLAMM et al., "XeF2 and F-Atom Reactions with Si: Their Significance for Plasma Etching", Solid State Technol. 26, 117 (1983).	
	DG	IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	
	DH	IBBOTSON et al., "Comparison of XeF2 and F-atom Reactions with Si and SiO2", Applied Physics Letter, Vol. 44, 1129 (1984).	
	DI	STRELLER et al., "Selectivity in Dry Etching of Si (100) and XeF2 and VUV Light", Elsevier Science B.V., Applied Surface Science Vol. 106 (1996), pp. 341-346.	
	DJ	VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
BNT	DK	Y.K. Fang, et al., The Compatibility of Aluminum Layers on Plasma-Deposited W and WSi2 Films, , 1988 IEEE, IEEE Transactions on Electron Devices, Vol. 35, No. 5, May 1988.	

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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Sheet 6 of 10

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First Named Inventor	Patel. et al
Group Art Unit	Not Yet Assigned
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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BNT	DL	WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	
	DM	WINTERS et al., "The Etching of Silicon with XeF2 Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
	DN	XACTIX, Inc., Marketing Brochure (June 27, 1999).	
	DO	"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
	DP	Assorted promotional literature, Surface Technology Systems Ltd., Newport, UK (July 28, 1999).	
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		G.J. van Gurp, et al., Aluminum-sillicide reactions. il. Diffusion, compound formation, and microstructure, 1979 American Institute of Physics, pgs 6915-6922.	
		J. Baglin, et al., An Alternative marker experiment in the formation of Mo and W silicides, 1978 American Institute of Physics. pgs 289-290.	
		M. Bartur, et al., Electrical characteristics of Al contact to NiSi using thin W layer as a barrier,, 1981 American Institute of Physics, pgs 822-824.	
		Krishna C. Saraswat, et al., Properties of Low-Pressure CVD Tungsten Silicide for MOS VLSI Interconnections, 1983 IEEE, pgs	
BNT		F. Mohammadi, et al.., Properties of Sputtered Tungsten Silicide for MOS Integrated Circuit Applications. pgs 450-454	

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Sheet 7 of 10

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Filing Date	Herewith
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Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092US

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BNT	BA	ANDERSON, H.M., "Plasma Diagnostics for Semicondcutor Processing", 2000 Digest of the LEOS Topical Meetings (July 24 - 28, 2000), pp. 117-118 (abstract only).	
	BB	BARYSHEV et al., "Monitoring of XiO2/Si Plasma Etching and End-Point Detection", Mikroelektronika (Russia), Vol. 25, No. 5 (Sept/Oct 1996), pp. 373-379 (abstract only).	
	BC	BASSOM et al., "Modeling and Optimizing XeF2-enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
	BD	BERG et al., "Real-Time Control of Etching Processes: Experimental Results", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 3213 (1997), pp. 249-260 (abstract only).	
	BE	CHAMBERS et al., "Endpoint Uniformity Sensing and Analysis in Silicon Dioxide Plasma Etching Using In Situ Mass Spectrometry", J. Vac. Sci. Technol. B, Microelectron. Nanometer Struct., Vol. 16, No. 6 (Nov/Dec 1998), pp. 2996-3002 (abstract only).	
	BF	CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millenium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
	BG	CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Socity for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	
	BH	CHEN et al., "Spatially Resolved Endpoint Detector for Plasma Etcher", 1997 IEEE International Symposium on Semiconductor Manufacturing Conference Proceedings, San Francisco, CA (Oct. 6 - 8, 1997), pp. B45 - B48 (abstract only).	
	BI	CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
	BJ	HEINRICH et al., "Multichannel Process Monitor for Real-Time Film Thickness and Rate Measurements in Dry Etching and Deposition", Vacuum, Vol. 51, No. 4, (Dec. 1998), pp. 497-502 (abstract only).	
BNT	BK	KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 8 of 10

Complete if Known	
Application Number	10/627,302
Filing Date	Herewith
First Named Inventor	Patel, et al
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092US

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
BNT	BL	LI et al., "Mass Spectometric Measurements on Inductively Coupled Fluorocarbon Plasmas: Positive Ions, Radicals and Endpoint Detection", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 5 (Sept. 1997), pp. 2438-2446 (abstract only).	
	BM	LIAMANOND et al., "Production Data Based Optimal Etch Time Control Design for a Reactive Ion Etching Process", IEEE Trans. Semicond. Manuf., Vol. 12, No. 1 (Feb. 1999), pp. 139-147 (abstract only).	
	BN	LITVAK, H.E., "End Point Control Via Optical Emission Spectroscopy", J. Vac. Sci. Technol. B, Microelectron. Nanometer Struct., Vol. 14, No. 1 (Jan/Feb 1996), pp. 516-520 (abstract only).	
	BO	LU et al., "Effluent Monitoring with FTIR Spectroscopy for Low Open Area Oxide Etch Endpoint Detection", 8th International Symposium on Simiconductor Silicon, San Diego, CA, Vol. 2 (May 4 - 8, 1998), pp. 1250-1261 (abstract only).	
	BP	MAYNARD et al., "Plasma Etching of Submicron Devices: In Situ Monitoring and Control by Multi-Wavelength Ellipsometry", Thin Solid Films (Switzerland), Vol. 313-314, No. 1-2 (Feb. 1998), pp. 398-405 (abstract only).	
	BQ	MELVILLE et al., "Volatile Products and Endpoint Detection in Reactive Ion Etching of III-V Compounds with a Broad Beam ECR Source", Nuclear Instruments & Methods in Physics Research, Section B (Beam Interactions with Materials and Atoms), Vol. B106, No. 1-4 (Dec. 1995), pp. 179-182 (abstract only).	
	BR	MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5-mu m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
	BS	PERRIN, J., "Mass Spectrometry of Reactive Plasmas", Plasma Processing of Semiconductors, Chateau de Bonas, France (June 17 - 28, 1996), pp. 397-431 (abstract only).	
	BT	RICHTER et al., "Exhaust Gas Monitoring: New Window Into Semiconductor Processing", Solid State Technol., Vol. 42, No. 5 (May 1999), pp. 61, 63-64, 68, 70-71 (abstract only).	
	BU	SAITO et al., "Low Temperature Plasmaless Etching of Silicon Dioxide Film Using Chlorine Trifluoride Gas with Water Vapor", J. Electrochem. Soc., Vol. 147, No. 12 (Dec. 2000), pp. 4630-4632 (abstract only).	
BNT	BV	SEBEL et al., "Etching of Si Through a Thick Condensed XeF2 Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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Sheet 9 of 10

Complete if Known	
Application Number	10/627,302
Filing Date	Herewith
First Named Inventor	Patel, et al
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	P092US

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
BNT	BW	SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
	BX	SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
	BY	SUGANO et al., "Study on XeF2 Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechantronics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
	BZ	SUN et al., "Sensitive Plasma Etching Endpoint Detection Using Tunable Diode Laser Absorption Spectroscopy", Appl. Phys. Lett., Vol. 64, No. 21 (May 23, 1994), pp. 2779-2781 (abstract only).	
	CA	THOMAS et al., "Minimized Response Time of Optical Emission and Mass Spectrometric Signals for Optimized Endpoint Detection", J. Vac. Sci. Technol. B, Microelectron. Nanometer Struct., Vol. 14, No. 4 (July/Aug 1996), pp. 2531-2536 (abstract only).	
	CB	TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
	CC	VUGTS et al., "Si/XeF2 Etching: Reaction Layer Dynamics and Surface Roughening", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 14, No. 5 (Sept/Oct 1996), pp. 2780-2789 (abstract only).	
	CD	VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 14, No. 5 (Sept/Oct 1996), pp. 2766-2774 (abstract only).	
	CE	WAN et al., "Electron Cyclotron Resonance Plasma Reactor for SiO2 Etching: Process Diagnostics, End-Point Detection, and Surface Characterization", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 13, No. 4 (July/Aug 1995), pp. 2035-2043 (abstract only).	
	CF	WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
BNT	CG	WARD, P.P., "Plasma Process Control with Optical Emission Spectroscopy", 17th IEEE/CPMT International Electronics Manufacturing Technology Symposium: Manufacturing Technologies - Present and Future, Austin, TX (Oct. 2 - 4, 1995), pp. 166-169 (abstract only).	

Examiner Signature	Brandi Thomas	Date Considered	8/2/04

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First Named Inventor	Patel. et al
Group Art Unit	Not Yet Assigned
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BNT	CH	WARNEKE, et al., "In Situ Characterization of CMOS Post-Process Micromachining", Sens. Actuators A, Phys. (Switzerland), Vol. A89, No. 1-2 (March 20, 2001), pp. 142-151 (abstract only).	
	CI	WELCH et al., "Breaking the 0.5 Percent Exposed Area Etch Endpoint Barrier", Semicond. Int., Vol. 19, No. 8 (July 1996), pp. 269-270, 272, 274, 276 (abstract only).	
	CJ	WODECKI, N.D., Low Open Area Multi-Layered Dielectric Film Etch Endpoint Detection Using EndPoint Plus (TM)", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 3882 (1999), pp. 231-238 (abstract only).	
	CK	WONG et al., "Endpoint Prediction for Polysilicon Plasma Etch Via Optical Emission Interferometry", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 15, No. 3, Pt. 2 (May/June 1997), pp. 1403-1408 (abstract only).	
BNT	CL	YUE et al., "Plasma Etching Endpoint Detection Using Multiple Wavelengths for Small Open Area Wafers", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 19, No. 1 (Jan. 2001), pp. 66-75 (abstract only).	

Examiner Signature	Brad Thomas	Date Considered	8/2/04

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INFORMATION DISCLOSURE CITATION PTO-1449	ATTY. DOCKET NO. P92-US	SERIAL NO. Not Yet Assigned
	APPLICANT Patel, et al.	
	FILING DATE 7/24/03	GROUP Not Yet Assigned

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
BNT	6,028,690	02/22/00	Carter, et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
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						☐	☐

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EXAMINER Brandi Thomas DATE CONSIDERED 8/2/04

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
BNT	6,522,454	02/18/03	Meier, et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
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